

N-Channel Enhancement Mode MOSFET

1. Product Information

1.1 Features

- ☒ Surface-mounted package
- ☒ Advanced trench cell design

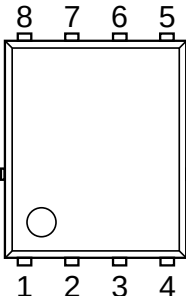
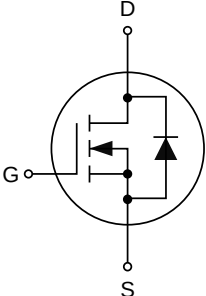
1.2 Applications

- ☒ LCD TV appliances
- ☒ High power inverter system
- ☒ LCDM appliances

1.3 Quick reference

- ☒ $BV \geq 150\text{ V}$
- ☒ $R_{DS(ON)} \leq 10.8\text{ m}\Omega @ V_{GS} = 10\text{ V}$
- ☒ $P_D \leq 156\text{ W}$
- ☒ $R_{DS(ON)} \leq 12.5\text{ m}\Omega @ V_{GS} = 8\text{ V}$
- ☒ $I_D \leq 75\text{ A}$

2. Pin Description

Pin	Description	Simplified Outline	Symbol
1,2,3	Source	 Top View PDFN5x6-8L	
4	Gate		
5,6,7,8	Drain		

2. Limiting Values

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	Drain-Source Voltage	$T_C=25^{\circ}\text{C}$	150	-	V
V_{GS}	Gate-Source Voltage	$T_C=25^{\circ}\text{C}$	-	± 20	V
I_D^*	Drain Current (DC)	$T_C=25^{\circ}\text{C}, V_{GS}=10\text{ V}$	-	75	A
		$T_C=100^{\circ}\text{C}, V_{GS}=10\text{ V}$	-	52	A
$I_{DM}^{*,**,***}$	Drain Current (Pulsed)	$T_C=25^{\circ}\text{C}, V_{GS}=10\text{ V}$	-	300	A
P_D^*	Drain power dissipation	$T_C=25^{\circ}\text{C}$	-	156	W
I_S	Continuous-Source Current	$T_C=25^{\circ}\text{C}$	-	75	A
E_{AS}^*	Single Pulsed Avalanche Energy	$V_{DD}=50\text{ V}, L=0.5\text{ mH}$	-	225	mJ
T_J, T_{stg}	Operating Junction and Storage Temperature Range		-55	150	$^{\circ}\text{C}$
$R_{\theta JA}^*$	Thermal Resistance-Junction to Ambient		-	60.5	$^{\circ}\text{C/W}$
$R_{\theta JC}^*$	Thermal Resistance-Junction to Case		-	0.8	

Notes:

- * Surface Mounted on 1 in² pad area, $t \leq 10\text{ sec.}$
- ** Pulse width $\leq 10\text{ }\mu\text{s}$, duty cycle $\leq 1\%$.
- *** Limited by bonding wire.

4. Marking Information

Product Name	Marking
KJ0915G	0915 YWWXXX YWW: Date Code

5. Ordering Code

Product Name	Package	Reel size	Tape width	Quantity(pcs)
KJ0915G	PDFN5×6-8L	13"	12 mm	5000

Note: KUIJIEXIN defines "Green" as lead-free (RoHS compliant) and halogen free (Br or Cl does not exceed 900 ppm by weight in homogeneous material and total of Br and Cl does not exceed 1500 ppm by weight; Follow IEC 61249-2-21 and IPC/JEDEC J-STD-020C)

6. Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0 V, I _{DS} =250 μA	150	-	-	V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250 μA	2	3	4	V
I _{DSS}	Drain Leakage Current	V _{DS} =120 V, V _{GS} =0 V	-	-	1	μA
I _{GSS}	Gate Leakage Current	V _{GS} =0 V, V _{GS} =±20 V	-	-	±100	nA
R _{DS(ON)} ^a	On-State Resistance	V _{GS} =10 V, I _{DS} =40 A	-	9.5	10.8	mΩ
		V _{GS} =8 V, I _{DS} =20 A	-	10.5	12.5	
R _G	Gate resistance	V _{GS} =0 V, V _{DS} =0 V, f=1 MHz	-	1.4	-	Ω
Diode Characteristics						
V _{SD} ^a	Diode Forward Voltage	I _{SD} =40 A, V _{GS} =0 V	0.7	1.0	1.3	V
t _{rr}	Reverse Recovery Time	I _{DS} =40 A, dI _{SD} /dt=100 A/μs	-	46	-	ns
Q _{rr}	Reverse Recovery Charge		-	48	-	nC
Dynamic Characteristics ^b						
C _{iss}	Input Capacitance	V _{GS} =0 V, V _{DS} =75 V f=1 MHz	-	2240	-	pF
C _{oss}	Output Capacitance		-	375	-	
C _{rss}	Reverse Transfer Capacitance		-	30	-	
t _{d(on)}	Turn-on Delay Time	V _{DS} =75 V, V _{GEN} =10 V, R _G =2.7Ω, I _{DS} =40 A	-	14.5	-	ns
t _r	Turn-on Rise Time		-	41	-	
t _{d(off)}	Turn-off Delay Time		-	24.5	-	
t _f	Turn-off Fall Time		-	9	-	
Gate Charge Characteristics ^b						
Q _g	Total Gate Charge	V _{DS} =75V, V _{GS} =10 V, I _{DS} =40 A	-	32.5	-	nC
Q _{gs}	Gate-Source Charge		-	13.5	-	
Q _{gd}	Gate-Drain Charge		-	6.8	-	

Notes:

a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.

b. Guaranteed by design, not subject to production testing.

7. Typical Characteristics

Fig 1: Output Characteristics

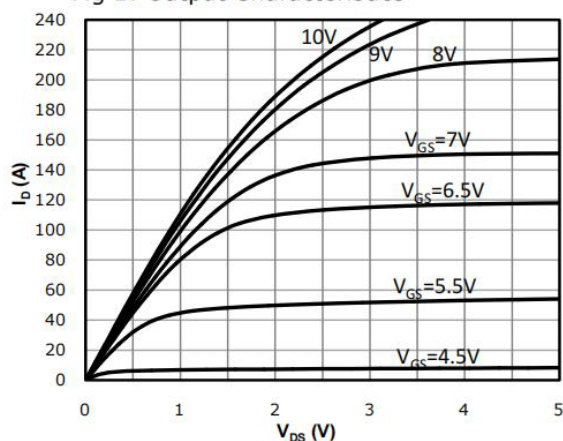


Fig 2: Transfer Characteristics

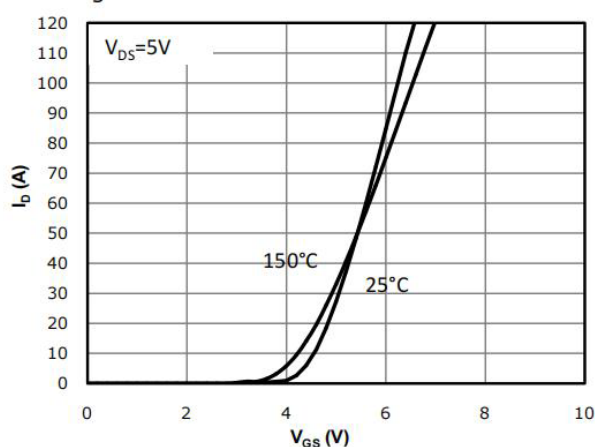


Fig 3: $R_{DS(on)}$ vs Drain Current and Gate Voltage

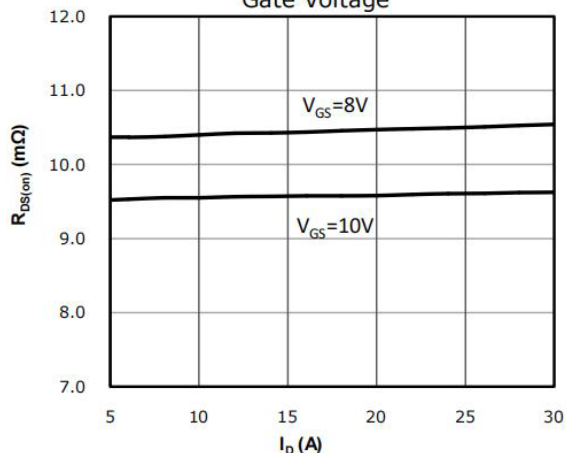


Fig 4: $R_{DS(on)}$ vs Gate Voltage

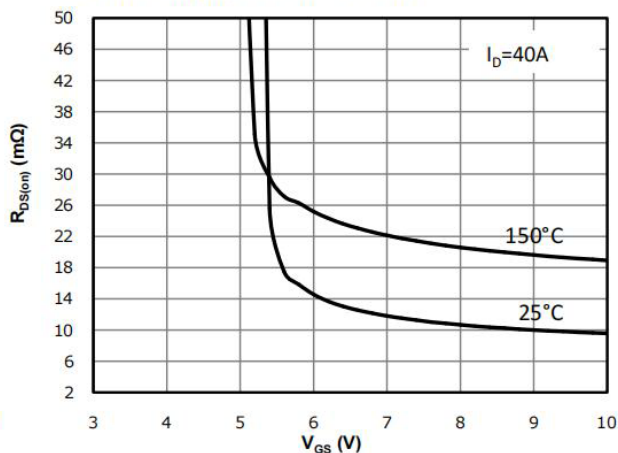


Fig 5: $R_{DS(on)}$ vs. Temperature

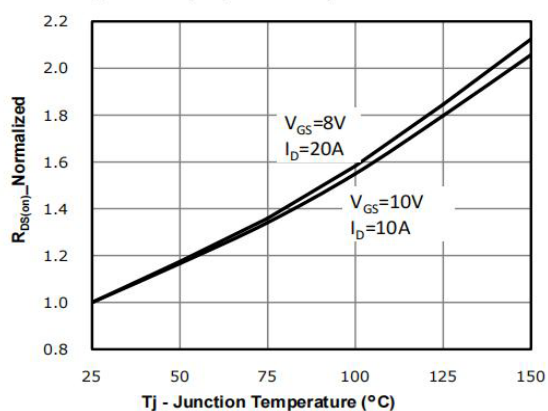
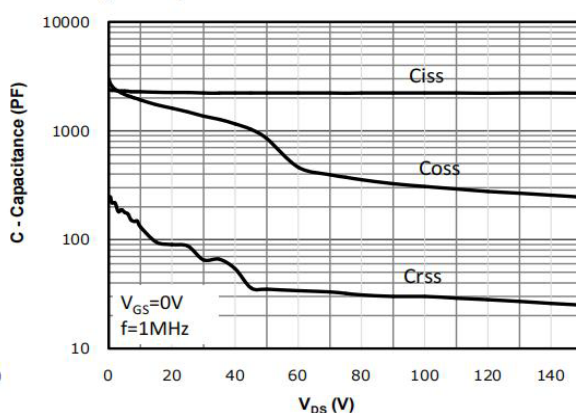


Fig 6: Capacitance Characteristics



7. Typical Characteristics (cont.)

Fig 7: Gate Charge Characteristics

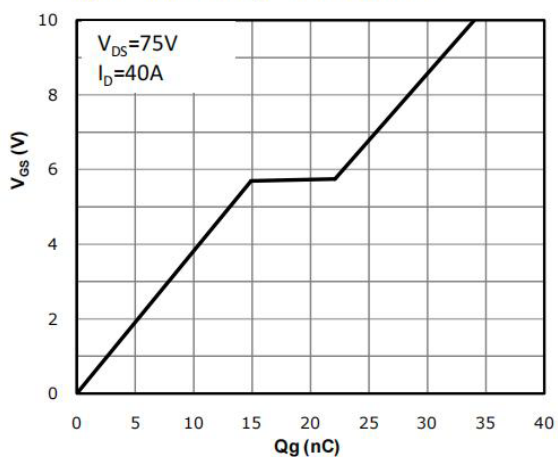


Fig 8: Body-diode Forward Characteristics

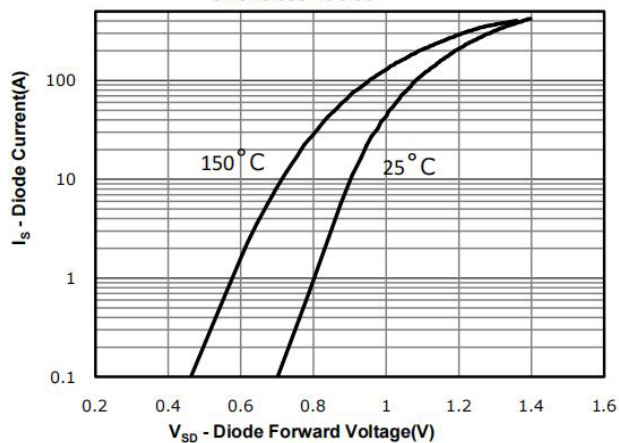


Fig 9: Power Dissipation

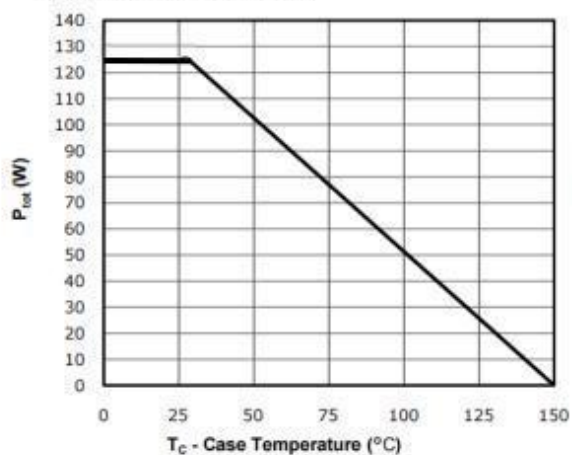


Fig 10: Drain Current Derating

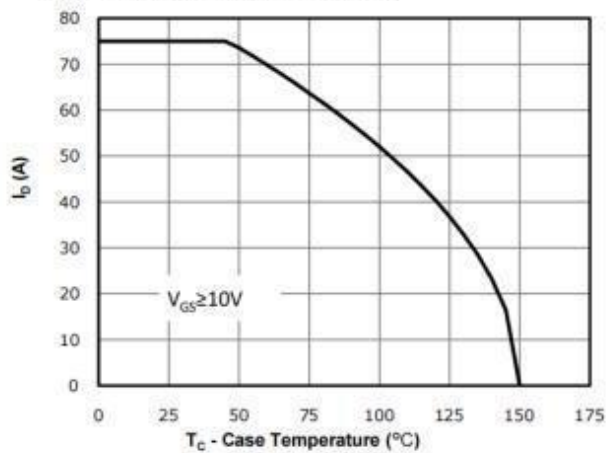
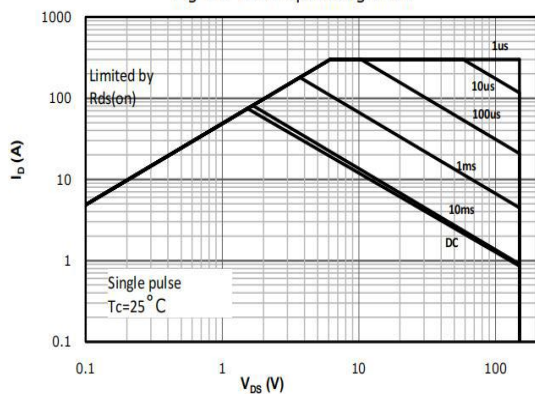
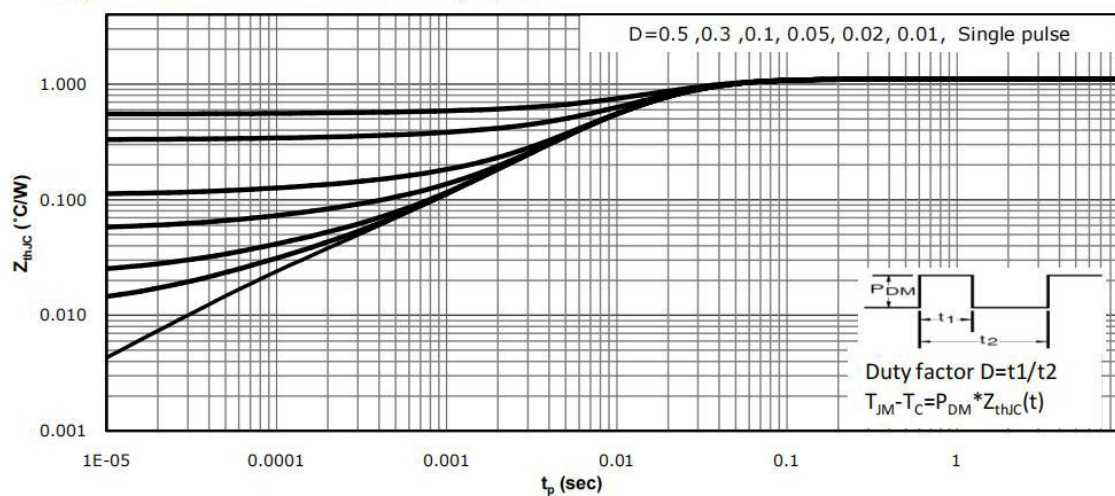


Fig 11: Safe Operating Area



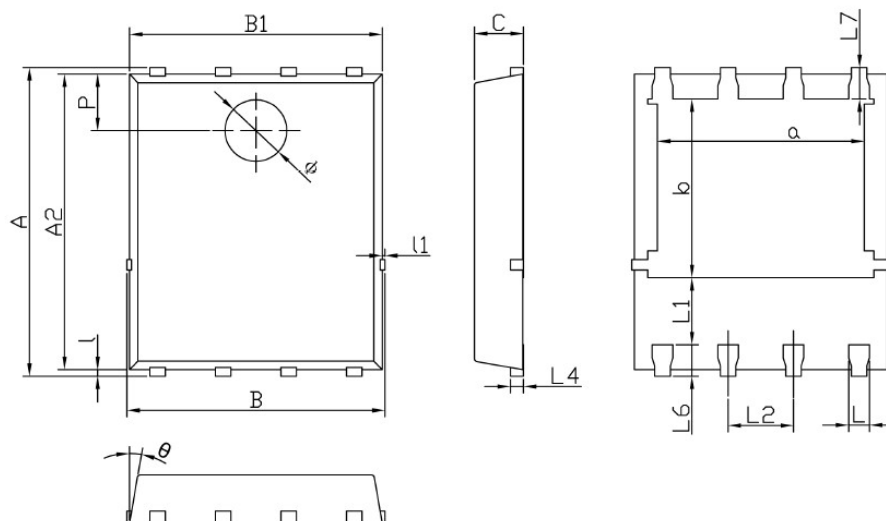
7. Typical Characteristics (cont.)

Fig 12: Max. Transient Thermal Impedance



8. Package Dimensions

PDFN 5x6-8L Package



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	5.90	6.10
A2	5.70	5.80
a	3.91	4.11
B	4.90	5.10
B1	4.80	5.00
b	3.37	3.57
C	0.90	1.00
e	0.06	0.20
e1	-	0.10
L	0.35	0.45
L1	1.10	-
L2	1.17	1.37
L4	0.21	0.34
L6	0.51	0.71
L7	0.51	0.71
P	1.00	1.20
Φ	1.10	1.30
θ	8°	12°